Edge States in p-n Junctions in Inverted Band HgTe Quantum Wells

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***Abstract*—We investigate current noise of lateral p-n junctions, electrostatically defined in 14 nm–wide HgTe-based quantum wells (QWs) with inverted band structure. Consistent with previous experiments on 8-10 nm QWs, the p-n junctions resistances are close to $h/2e^2$, indicating the edge states contribution to transport. Taking into account contacts heating, we find that the observed shot noise is suppressed compared to the diffusive value and is in reasonable agreement with prediction for one-dimensional edge states realized along the p-n junction. Our approach looks promising for the study of short quasi-ballistic edges in topological insulators (TIs).**

I. Introduction

Theoretical prediction for the possible existence of gapless edge states on the boundary between a topologically nontrivial and a conventional insulators [1] has led to their experimental realization in several materials [2], [3]. Concerning the HgTe QWs with inverted band structure, edge transport was verified, e.g., via non-local measurements [4] or the visualisation of current density [5]. Despite extensive study, however, some fundamental aspects are still lacking understanding. Edge conductance values, close to the quantum e^2/h, were demonstrated only for the shortest edges no longer than few micrometers [2], [6]. Up to now there is no agreement on the dominant scattering mechanism, which leads to the linear length-dependence with the absent or weak dependence on temperature for the longer edges [7]. Our objective here is to implement noise measurements for the study of edge states.

The nature of edge conduction mechanism may be directly probed by the measurements of current fluctuations, which are induced by the scattering of electrons transmitted through the conductor. For example, for strictly one dimensional coherent conductor, the Fano-factor $F = S_I/2eI$ is directly related to the transmission via $F = 1 - \mathcal{T}$. For a ballistic conductor shot noise vanishes, while in diffusive multi-channel regime $F = 1/3$. Despite the obvious potential of shot noise measurements, to the best of our knowledge there is only one experimental study considering current noise of the edge states [8]. The authors examined relatively long resistive edges and obtained F between 0.1 and 0.3, qualitatively consistent with the later developed theory [9]. Up to now, vanishing shot noise – the direct consequence and evidence of ballistic transport, was never observed for edges with $R_{\rm edge} \approx h/e^2$.

Recently, the edge states contribution [10], [11] was experimentally identified in the conductance of lateral $p-n$ junctions in $8-10\,\mathrm{nm}$ HgTe QWs [12]. Here, we investigate the current noise of such junctions, defined electrostatically in 14 nm HgTe QWs at $T = 0.5\,\mathrm{K}$. While for 8 nm QWs this is a low enough temperature to safely exclude the bulk shunt of edge states transport, an order of magnitude smaller bulk gap in 14 nm QWs requires even lower temperatures. We therefore intentionally limit ourselves to the discussion of short $p-n$ junctions. We demonstrate the importance of (i) minimizing the contacts resistance and (ii) hole-phonon scattering, characterized by the rate $\Sigma_{\rm h-ph}$, in p-type conduction region. Our approach, provided $\Sigma_{\rm h-ph}$ is known, may allow to infer the edge transport mechanism.

Theoretical values $F = 0$ and $F = 1/3$ [13] (or $F = \sqrt{3}/4$ in the case of strong electron-electron scattering) obtained for ballistic and diffusive conductors, respectively, hold assuming ideal boundary conditions for the electrons immediately at the sample ends, i.e. for reservoirs of infinite size with infinite electric and heat conductivities [14]. Experimentally, however, the measured signal may be significantly affected by overheating of the leads, which depends on its material, actual size and heat conductance. Qualitatively, in the presence of current flow, the Johnson-Nyquist noise is no longer constant with current but grows with bias. For example, for the otherwise noiseless ballistic conductor connected in series with realistic supply leads, this overheating is twofold. First, the temperature of the contact 2D leads itselves grows in accordance with the total dissipated Joule heat. This, in turn, modifies the electronic distribution function at the ends of the ballistic conductor and thus leads to further noise increase. This effect was observed as the measured noise increase for diffusive wires connected to rerservoirs with insufficient heat conductance [14], or as finite noise on the conductance plateaus [15]–[18] of ballistic quantum point contacts. The magnitude of this stray noise temperature increase is determined by the ratio of conductor's and 2D leads resistances. Concerning available shot noise experiments on HgTe QWs, while overheating effect is not significant for long resistive edges ($R_{\rm edge}/R_{\rm cont} \approx 10$) [8], it is not the case in the present study ($R_{\rm pn}/R_{\rm cont} \lesssim 3$). As a result, the proper consideration of reservoir noise is of great importance here. In the following, we first describe our samples; then discuss the transport indications of edge contribution to $p-n$ junctions conductance; then study reservoirs heating in response to the flowing current; and, finally, discuss the

obtained results for the noise of $p-n$ junctions.

II. Samples and measurement technique

Our samples are based on 14 nm wide (112) CdHgTe/HgTe/CdHgTe QWs grown by molecular beam epitaxy, with mesas shaped by wet etching and covered with a SiO_2/Si_3N_4 insulating layer, see Ref. [19] for the details. Metallic Au/Ti top gates enable us to tune the 2D system across the charge neutrality point by means of field effect. Ohmic contacts are achieved by a few second In soldering in air, providing a typical resistance of the ungated mesa arms $\approx 5\,\mathrm{k}\Omega$ at low T. The experiment was performed in a liquid ^{3}He insert with a bath temperature $T = 0.5\,\mathrm{K}$. Transport measurements were performed in a two-terminal or multi-terminal configurations with a low-noise $100\,\mathrm{M}\Omega$ input resistance preamplifier. The voltage fluctuations were measured within a frequency band $20-24\,\mathrm{MHz}$ for sample S1 and $8.5-9.5\,\mathrm{MHz}$ for sample S2 on a $R_0 = 10\,\mathrm{k}\Omega$ load resistor, connected in parallel with 22 MHz (9 MHz) resonant tank circuit. The signal was amplified by a home-made 10 dB low-temperature amplifier (LTAmp), followed by a $3\times 25\,\mathrm{dB}$ room-T amplification stage, and measured with a power detector (not shown in fig. 1a). The setup was calibrated via the Johnson-Nyquist thermometry. Below we present the results obtained on two samples which demonstrate similar behavior reproducible with respect to thermal recycling. We note that transport measurements were also performed on two more samples with similar results.

III. Transport measurements

The samples layouts are shown schematically in fig. 1a,b with 2D leads coloured in gray and electrostatic gates in yellow. Sample S1 is equipped with one large gate, while sample S2 is equipped with two smaller gates, only one of which (labeled with G) was used in the present experiment. Via indexed letters Ci we denote 2D mesa leads (see the sketch of the whole sample S2 in the inset of fig. 1c). Contact labeled with N was used for noise measurements. From four-point resistance measurements at gate voltages $V_\mathrm{g} = 0\,\mathrm{V}$ and $V_\mathrm{g} = -6\,\mathrm{V}$ we extract the electron (hole) resistivities ρ_e (ρ_h) of $230\,(2000)\,\Omega$ for sample S1 and $240\,(3200)\,\Omega$ for sample S2.

In fig. 1c we plot the gate voltage dependencies of the two terminal linear response resistances ($R_{2\mathrm{t}}$) for several contacts on both samples S1 and S2. In these measurements all contacts, except for the studied one, are grounded. At $V_\mathrm{g} = 0\,\mathrm{V}$ the measured value, $R_{2\mathrm{t},e}$, reflects the resistance of 2D mesa leads and ohmic contacts at the In/2DEG interface (which we denote via $R_{\mathrm{Ci/N,ohmic}}$). It is on the order of a few kiloohms for most of the contacts. However, contacts C4 and C5 of sample S2 were not not working, probably, due to poor In soldering, and contacts C6 and C7 of sample S2, as well as contact C3 of sample S1, had relatively large resistances of approximately $20\,\mathrm{k}\Omega$, $70\,\mathrm{k}\Omega$ and $20\,\mathrm{k}\Omega$, respectively.

At negative enough V_g, when p-type conduction regime is set up in the mesa region under the gate, the measured

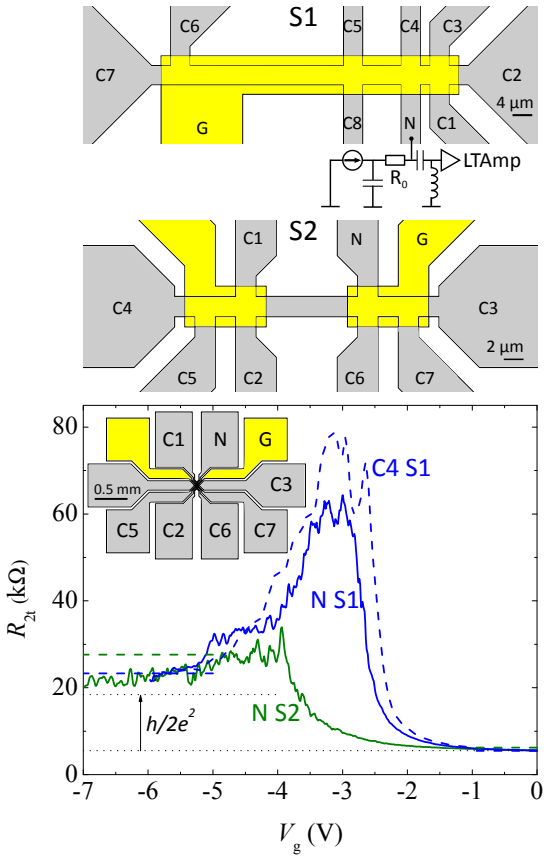

Fig. 1. Sample schematics and two-terminal resistance of our samples. (a,b) Schematic representation of the samples S1 and S2 with measurement scheme. (c) Two-terminal resistance for indicated contacts. The dashed curve (contact C4 S1) is shifted by $2.8\,\mathrm{k}\Omega$. The inset shows the layout of the whole sample S2.

resistance, $R_{2\mathrm{t},h}$, is determined simultaneously by ohmic contacts, 2D leads, p-type conduction area under the gate and $p-n$ junctions, formed in the mesa under the gate edge. For all samples studied, $R_{2\mathrm{t},h}$ is almost V_g-independent, though with visible fluctuations, at $V_\mathrm{g} < -5\,\mathrm{V}$. While both $R_{2\mathrm{t},e}$ and $R_{2\mathrm{t},h}$ values may be affected by the unknown ohmic contact resistance, their difference eliminates this uncertainty and provides information about $p-n$ junctions resistances. We note that for most contacts for all samples the difference $R_{2\mathrm{t},h} - R_{2\mathrm{t},e}$ is always close to $R_Q \equiv h/2e^2$, exceeding it by several kiloohms, which may correspond to the resistance of under-the-gate p-type conduction region.

Assuming all $p-n$ junctions have resistance $R_\mathrm{pn} = R_Q$ and using measured values of $\rho_{e,h}$, for geometry corresponding to mesa mask we calculate the two terminal resistance (for both n- and p-type conduction under the gate) for different contacts, and compare it with experimental values. The calculated values are illustrated in fig. 1c by thick dashed straight lines. For contact N on sample S1 thus calculated resistance is perfectly consistent with the measured value both at $V_\mathrm{g} = 0\,\mathrm{V}$ and $V_\mathrm{g} = -6\,\mathrm{V}$ in assumption of vanishing corresponding ohmic contact resistance $R_\mathrm{N,ohmic} = 0\,\Omega$. For contact C4

on sample S1 both measured resistances are greater than calculated values by the same amount of $\approx 2.8\,\mathrm{k}\Omega$, which most likely reflects $R_{\mathrm{C4,ohmic}} = 2.8\,\mathrm{k}\Omega$. This consistency shows that the resistance of $p-n$ junctions in our devices is indeed close to resistance quantum. For contact N on sample S2, while the agreement for n-type conduction is good with negligibly small $R_{\mathrm{N,ohmic}} = 0\,\Omega$, the measured resistance for p-type conduction under the gate is by $\sim 4\,\mathrm{k}\Omega$ smaller than the calculated one. This might indicate the bulk of $p-n$ junction contribution to transport. We note that observation $R_{\mathrm{pn}} \approx R_Q$ holds also for samples where noise measurements were not performed.

The values $R_{\mathrm{pn}} \approx R_Q$ do not necessarily imply that conduction through $p-n$ junctions is realized via two ballistic single-channel edge states. In the following we study shot noise at large negative V_g and compare obtained results with two limit predictions, corresponding to either ballistic or diffusive conduction across the $p-n$ junction.

IV. Noise measurements

A. Contacts heating

First, in order to take contacts heating into account, we set $V_g = 0\,\mathrm{V}$ and study 2D leads heating in response to the flowing current. For long enough conductors, when local electron temperature is well defined, shot noise is represented by the Johnson-Nyquist relation with electron temperature averaged over the whole sample. Experimental results, expressed in terms of noise temperature $T_N = S_I R/4k_B$, are shown in fig. 2 for sample S2 by circles. To demonstrate the influence of inelastic e-ph scattering, by dotted line we show the prediction for the case, when e-ph scattering is absent. The obvious T_N suppression reflects the fact that thermal relaxation of electrons is realized not only by electronic diffusion towards the ohmic contacts, but also by electron-phonon coupling. Local power flow between electron and phonon systems is given by

$$P_{\mathrm{e-ph}} = \Sigma_{\mathrm{e-ph}}(T^\alpha - T_0^\alpha),$$

where $T = T(x,y)$ – position-dependent electronic temperature, T_0 – bath temperature and $\Sigma_{\mathrm{e-ph}}$ is material-dependent electron-phonon coupling coefficient. Exponent α characterizes the heat transfer mechanism and in general varies in the range $\alpha \approx 3-6$ [20]. To determine the exact values of $\Sigma_{\mathrm{e-ph}}$ and α, we first numerically solve the two-dimensional stationary heat diffusion equation

$$-\nabla(\varkappa \nabla T) = Q_{\mathrm{Joule}} - P_{\mathrm{e-ph}}$$

along with Poisson's equation, for the sample shape corresponding to the lithographic mesa pattern. Here $Q_{\mathrm{Joule}} = \mathbf{j}\cdot\mathbf{E}$ – local Joule heat power source, $\mathcal{L} = 2.44\times10^{-8}\,\mathrm{W\Omega K^{-2}}$ – the Lorenz number, and heat conduction is assumed to satisfy the WiedemannFranz law

$$\varkappa = \sigma\mathcal{L}T.$$

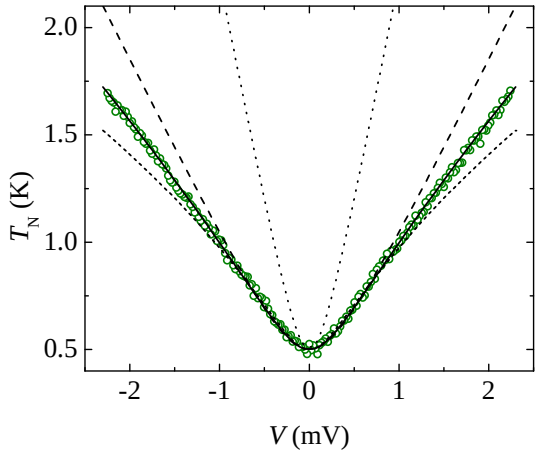

Fig. 2. Contacts heating study. Noise temperature as a function of bias voltage (symbols) at $V_g = 0\,\mathrm{V}$. Dotted line is the prediction for the case when e-ph scattering is absent. Dashed, solid and short-dashed lines correspond to power-law heat transfer between electron and phonon systems with exponent $\alpha = 2$, 3 and 4, respectively.

Using thus obtained electronic temperature profile, we calculate the noise temperature of the sample via

$$T_N = \frac{\int T(x,y)\,Q_{\mathrm{Joule}}\,\mathrm{d}x\mathrm{d}y}{\int Q_{\mathrm{Joule}}\,\mathrm{d}x\mathrm{d}y}, \qquad (1)$$

with integration taken over the whole mesa.

We find that in the bias voltage range of few millivolts experimental data are best fitted with $\alpha \approx 3$ (see fig. 2). The corresponding value of $\Sigma_{\mathrm{e-ph}} = 16\,\mathrm{mW/m^2K^3}$ is the same for both samples S1 and S2 and is reproducible with respect to thermal recycling. Passing, we note that for larger bias voltages up to $\sim 100\,\mathrm{mV}$ the data are perfectly consistent with $\alpha = 4$ and $\Sigma_{\mathrm{e-ph}} \approx 7\,\mathrm{mW/m^2K^4}$. Both exponents $\alpha = 3$ and $\alpha = 4$ may correspond to the 2D acoustic phonon cooling mechanism and were observed, for example, in graphene [21], [22].

B. Shot noise of $p-n$ junctions

We next discuss results obtained for large negative gate voltages, when p-type conduction regime is set up in the mesa region under the gate. Here, $p-n$ junctions are formed in the mesa region close to the gate edges. As discussed above, these $p-n$ junctions are connected to ohmic contacts not only via 2D leads with n-type conduction, but in part also via more resistive p-type conduction region under the gate. Unfortunately, the geometry of our samples doesn't allow to accurately determine the rate of hole-phonon energy relaxation $\Sigma_{\mathrm{h-ph}}$. We are not aware of any systematic studies of $\Sigma_{\mathrm{h-ph}}$ in HgTe QWs, however, there are some indications from transport-based measurements of energy relaxation that the hole-phonon energy relaxation is significantly enhanced compared to $\Sigma_{\mathrm{e-ph}}$ [23]. In the following we compare experimentally obtained results with model predictions for various values of $\Sigma_{\mathrm{h-ph}}$.

Our model geometry (see fig. 3) corresponds to mesa mask geometry with dotted rectangular indicating the gate position.

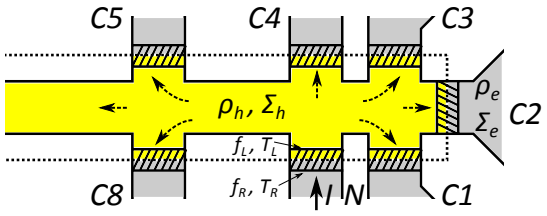

Fig. 3. Model for calculations. Dotted line shows the gate boundary. We fix the temperatures $T = T_0$ and electric potentials $\varphi_N = V$, $\varphi_{Ci} = 0$ at ohmic contacts (not shown in the figure).

Yellow area is the p-type conduction region under the gate with hole resistivity ρ_h and hole-phonon coupling $\Sigma_{\rm h-ph}$; gray areas are the n-type conduction 2D leads with electron resistivity ρ_e and electron-phonon coupling $\Sigma_{\rm e-ph}$. Shaded rectangles at the edge of the gate model $p-n$ junctions with conductance $G = G_Q \equiv 2e^2/\hbar$. We note that calculation results do not depend on the length of the $p-n$ junction area as long as it is reasonably short, thus allowing to neglect phonon scattering in this region. We set boundary conditions by defining temperatures $T = T_0$ at the ohmic contacts. The bias voltage, V, applied to the N-contact, defines the current through each mesa arm, allowing the temperature map to be obtained from the combined solution of Poisson's and heat diffusion equations. This is enough to calculate the noise temperature of the sample as we describe below.

Generally, noise power of the current fluctuations in the non-interacting scattering theory is determined by two inputs [24]:

$$S = S_{\rm eq} + S_{\rm non-eq},$$

where the first term is the analog of the equilibrium noise contribution, present for any conductor –

$$S_{\rm eq} = G_Q \sum_n \int {\rm dE}\left\{T_n\left[f_L(1-f_L) + f_R(1-f_R)\right]\right\},$$

and the second term is the non-equilibrium or shot noise contribution –

$$S_{\rm non-eq} = G_Q \sum_n \int {\rm dE}\left\{T_n(1-T_n)\left(f_L - f_R\right)^2\right\}.$$

We consider two limit predictions for the noise of our $p-n$ junctions. The first one corresponds to ballistic conduction across the $p-n$ junction (along two mesa edges), when it's current spectral density is completely determined by $S_{\rm eq}$:

$$S_{\rm ball} = 2G_Q \int dE\left[f_L(1-f_L) + f_R(1-f_R)\right].$$

We assume electronic distribution functions at the boundaries of the $p-n$ junction to be Fermi-Dirac with temperatures T_L and T_R, that are obtained numerically from the solution of heat diffusion equation. Such an assumption ensures the proper heat flow outwards the $p-n$ junction. The current spectral density of the $p-n$ junction is thereby given by

$$S_{\rm ball} = 2k_B(T_L + T_R)G_Q.$$

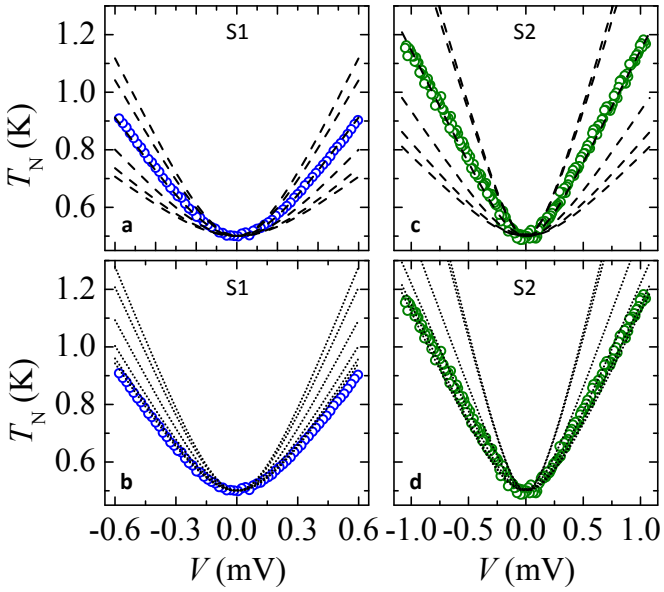

Fig. 4. Noise measurements at negative gate voltages. (a,b) Shot noise measured with contact N on the sample S1 (symbols). Lines are the fits for the hole-phonon couplings $\Sigma_{\rm h-ph} = 0;\ 0.016;\ 0.14;\ 1.4;\ 14;\ 140\,{\rm W/m^2K^3}$ (from top to bottom) for the case of (a) ballistic (dashed) and (b) diffusive (dotted) noise of the $p-n$ junction. (c,d) The same for the sample S2 with corresponding $\Sigma_{\rm h-ph} = 0;\ 0.016;\ 0.23;\ 2.3;\ 23;\ 230\,{\rm W/m^2K^3}$.

Another limit is realized when conduction across the $p-n$ junction is diffusive. Here, current spectral density is determined both by equilibrium and shot noise contributions, and can be calculated via eq.(1):

$$S_{\rm diff} = 4k_B T_N G_Q.$$

The noise of contacts is also calculated via eq.(1). For both limits we treat 2D leads and $p-n$ junctions as uncorrelated noise sources and calculate the noise temperature of the sample using standard formalism [24]. We note that the two-terminal differential resistance of our samples at large negative gate voltages is almost bias-independent, with changes on the order of few percent. This behaviour is in contrast with behaviour of typical semiconductor $p-n$ junctions and may serve as an additional indication for the edge states shunting the bulk of the $p-n$ junctions.

Experimental results (symbols), obtained for sample S1 at $V_g = -6.5\,{\rm V}$ and for sample S2 at $V_g = -6\,{\rm V}$, are shown in fig. 4a,b and fig. 4c,d, respectively (note a wider bias range for the sample S2). These results are almost V_g-independent for large negative V_g. We emphasize that the data slope $dS_I/d(2eI) \approx 0.15$ should not be confused with the Fano-factor of the $p-n$ junctions, since the measured signal is comprised of both the junction and the contact noise inputs. The fits for ballistic and diffusive conduction across the $p-n$ junctions are shown in fig. 4a,c and fig. 4b,d by dashed and dotted lines, respectively. Since $\Sigma_{\rm h-ph}$ is unknown, we compare experimental results with model predictions for different strength of hole-phonon coupling. We note that for the values of $\Sigma_{\rm h-ph} \approx \Sigma_{\rm e-ph}$ the model prediction is much

greater than experimentally observed value even in the ballistic case, indicating that $\Sigma_{\mathrm{h-ph}} \gg \Sigma_{\mathrm{e-ph}}$. While for the ballistic case the model is in agreement with experimental data for the relatively reasonable values of $\Sigma_{\mathrm{h-ph}}(S1) = 0.14\,\mathrm{W/m^2K^3}$ and $\Sigma_{\mathrm{h-ph}}(S2) = 0.23\,\mathrm{W/m^2K^3}$, for the diffusive case the model prediction is still greater than experimentally observed values even for the three orders of magnitude stronger hole-phonon couplings and only approaches it at further $\Sigma_{\mathrm{h-ph}}$ increase. Although not providing definite value for the shot noise of $p-n$ junctions, the presented data suggest that it is suppressed compared to the diffusive value and is in reasonable agreement with prediction for one-dimensional edge states realized along the p-n junction.

V. Conclusion

In summary, we studied the current noise of lateral $p-n$ junctions, electrostatically defined in 14 nm–wide HgTe-based QWs. Resistance measurements indicate that the transport across the junction may be realized via two edge channels with resistance of each close to h/e^2. We take into account the contacts heating effect and compare experimental results for the shot noise with the model predictions for ballistic and diffusive junctions. Due to the unknown hole-phonon coupling our conclusion is not definitive, however, the obtained results support the presence of one-dimensional edge states in the p-n junction. Our approach looks promising for the study of short edges of 2D TIs.

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